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(54) **SEMICONDUCTOR INTEGRATED CIRCUIT, SEMICONDUCTOR STORAGE DEVICE, MEMORY SYSTEM, AND FREQUENCY GENERATION METHOD**

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(57) **ABSTRACT**

A semiconductor integrated circuit includes a first oscillator configured to generate a first signal with a first frequency based on a control signal and output the first signal to a path. The semiconductor integrated circuit includes a control signal generation circuit operatively coupled to the first oscillator via the path, and configured to receive the first signal from the first oscillator via the path and generate the control signal. The semiconductor integrated circuit includes a second oscillator configured to generate a second signal with a second frequency based on the control signal and output the second signal to an output terminal outside the path.